



## AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application.

Claims 1-30 (Cancelled)

31. (New) A wafer processing apparatus comprising:
- a plurality of chemical vapor deposition chambers, the chemical vapor deposition chambers to deposit metal layers on wafers by chemical vapor deposition;
- one or more annealing chambers, the one or more annealing chambers integrated with the wafer processing apparatus, the one or more annealing chambers to anneal the metal layers to stabilize hardness of the metal layers prior to chemical mechanical polishing;
- a robot to move the wafers having the metal layers deposited thereon; and
- logic to cause the robots to move the wafers having the metal layers deposited thereon from the chemical vapor deposition chambers directly to the one or more annealing chambers shortly after the metal layers have been deposited on the wafers.
32. (New) The wafer processing apparatus of claim 31, wherein the wafer processing apparatus consists essentially of the plurality of chemical vapor deposition chambers, the one or more annealing chambers, the robot, and the logic.
33. (New) The wafer processing apparatus of claim 31, wherein the one or more annealing chambers are attached to the side of the wafer processing apparatus.
34. (New) The wafer processing apparatus of claim 31, wherein the one or more annealing chambers are provided adjacent to the wafer processing apparatus and its chemical vapor deposition chambers.

35. (New) The wafer processing apparatus of claim 31, wherein the chemical vapor deposition chamber comprises a copper deposition chamber.
36. (New) The wafer processing apparatus of claim 31, wherein the annealing chamber comprises a furnace.
37. (New) The wafer processing apparatus of claim 31, wherein the annealing chamber comprises a heat lamp.
38. (New) The wafer processing apparatus of claim 31, wherein the annealing chamber comprises a hot stage.
39. (New) The wafer processing apparatus of claim 31, wherein the one or more annealing chambers are to heat the metal layer to a temperature of about 200 degrees Celsius.
40. (New) A wafer processing apparatus comprising:
  - one or more annealing chambers, the one or more annealing chambers integrated with the wafer processing apparatus, the one or more annealing chambers to anneal wafers having metal layers thereon to stabilize hardness of the metal layers prior to chemical mechanical polishing;
  - one or more chemical mechanical polishing platforms, the one or more chemical mechanical polishing platforms integrated with the wafer processing apparatus, the one or more chemical mechanical polishing platforms to polish the wafers including the metal layers;
  - a robot to move the wafers having the metal layers deposited thereon; and
  - logic to cause the robot to move the wafers having the metal layers deposited thereon from the one or more annealing chambers directly to the one or more chemical mechanical polishing platforms.

41. (New) The wafer processing apparatus of claim 40, further comprising logic to cause the robot to move the wafers from the one or more chemical mechanical polishing platforms to back to the annealing chamber after the wafers have been polished.
42. (New) The wafer processing apparatus of claim 40, wherein the wafer processing apparatus consists essentially of the one or more annealing chambers, the one or more chemical mechanical polishing platforms, the robot, and the logic.
43. (New) The wafer processing apparatus of claim 40, wherein the one or more annealing chambers are attached to the side of the wafer processing apparatus.
44. (New) The wafer processing apparatus of claim 40, wherein the one or more annealing chambers are provided adjacent to the wafer processing apparatus and one or more chemical mechanical polishing platforms.
45. (New) The wafer processing apparatus of claim 40, wherein the annealing chamber comprises one or more selected from a furnace, a heat lamp, and a hot stage.
46. (New) The wafer processing apparatus of claim 40, wherein the one or more annealing chambers are to heat the metal layer to a temperature of about 200 degrees Celsius.
47. (New) A wafer processing apparatus comprising:  
  
one or more chemical mechanical polishing platforms, the one or more chemical mechanical polishing platforms integrated with the wafer processing apparatus, the one or more chemical mechanical polishing platforms to polish wafers having metal layers thereon;  
  
one or more annealing chambers, the one or more annealing chambers integrated with the wafer processing apparatus, the one or more annealing chambers to

anneal wafers having the metal layers thereon to stabilize hardness of the metal layers after the wafers have been polished;

a robot to move the wafers; and

logic to cause the robot to move the wafers that have been polished from the one or more chemical mechanical polishing platforms directly to the one or more annealing chambers.

48. (New) The wafer processing apparatus of claim 47, further comprising logic to cause the robot to move the wafers from the one or more annealing chambers to the one or more chemical mechanical polishing platforms before the wafers have been polished.
49. (New) The wafer processing apparatus of claim 47, wherein the wafer processing apparatus consists essentially of the one or more annealing chambers, the one or more chemical mechanical polishing platforms, the robot, and the logic.
50. (New) The wafer processing apparatus of claim 47, wherein the one or more annealing chambers are attached to the side of the wafer processing apparatus.
51. (New) The wafer processing apparatus of claim 47, wherein the one or more annealing chambers are provided adjacent to the wafer processing apparatus and one or more chemical mechanical polishing platforms.